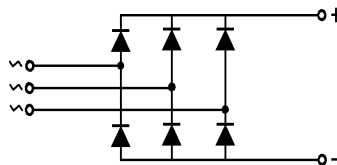


Three Phase Rectifier Bridge

Features

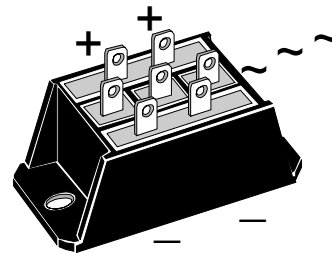
- International standard package
- With DBC ceramic base plate
- Planar passivated chips
- High surge capability



I_{dAVM} = 70A
V_{RRM} = 1200V- 1600V

Benefits

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Field supply for DC motors
- Battery DC power supplies



Absolute Maximum Ratings

I_{dAV} ①	T _c = 85°C, module		72	A
I_{dAVM} ①	module		75	A
I_{FSM}	T _{VJ} = 45°C; V _R = 0	t = 10 ms (50 Hz), sine	600	A
		t = 8.3 ms (60 Hz), sine	650	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine	540	A
		t = 8.3 ms (60 Hz), sine	600	A
I²t	T _{VJ} = 45°C V _R = 0	t = 10 ms (50 Hz), sine	1800	A ² s
		t = 8.3 ms (60 Hz), sine	1770	A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10 ms (50 Hz), sine	1460	A ² s
		t = 8.3 ms (60 Hz), sine	1510	A ² s
T_{VJ}			-40...+125	°C
T_{VJM}			125	°C
T_{stg}			-40...+125	°C
V_{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min	3000	V~
		t = 1 s	3600	V~
M_d	Mounting torque	(M5)	2-2.5	Nm
		(10-32 UNF)	18-22	lb.in.
Weight	typ.		50	g

Symbol	Test Conditions	Characteristic Values
I_R	$V_R = V_{RRM}; T_{VJ} = 25^\circ\text{C}$	0.3 mA
	$V_R = V_{RRM}; T_{VJ} = T_{VJM}$	5 mA
V_F	$I_F = 150\text{ A}; T_{VJ} = 25^\circ\text{C}$	1.9 V
V_{T0}	For power-loss calculations only	0.8 V
r_T		6.5 mΩ
R_{thJC}	per diode, DC current	1.2 K/W
	per module	0.2 K/W
R_{thJH}	per diode, DC current	1.6 K/W
	per module	0.27 K/W
d_s	Creep distance on surface	10 mm
d_A	Strike distance in air	9.4 mm
a	Max. allowable acceleration	50 m/s ²

Case Outline - MDS-pak

